

ASC900N1700MED

1700V, 900A, 2.8mΩ, Half-Bridge, Silicon Carbide MOSFET Module

Product Data Sheet

ASTC-3T03-26A A/0



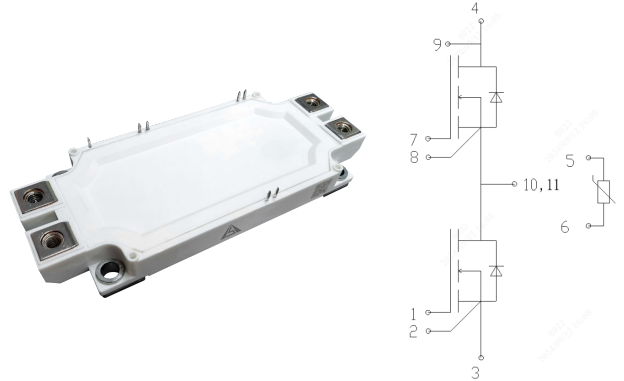
爱仕特科技
AST TECHNOLOGY

General Description

The AST-MED module incorporates AST's 1700V Gen3 N-channel SiC MOSFET. NTC temperature sensor inside.

Features

- High Temperature, Humidity, and Bias Operation
- Ultra Low Loss
- High-frequency Operation
- Zero Turn-off Tail Current from MOSFET
- Normally-off, Fail-safe Device Operation
- Copper Baseplate and Aluminum Nitride Insulator



Applications

- High Power Converters
- Motor Drives
- Servo Drives
- UPS Systems
- Wind Turbines

Ordering Informations

Order Number	ASC900N1700MED
Marking	ASC900N1700MED
Package Type	MED

Key Parameters

Symbol	Parameter	Values			Unit	Test Conditions
Absolute maximum rating						
V _{DS}	Drain-source Voltage	1700			V	T _C =25°C
I _D	Drain Current (continuous)	900			A	T _C =25°C
T _J	Junction Temperature	175			°C	
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics						
R _{DS(on)}	Static Drain-source on Resistance	-	2.8	3.4	mΩ	V _{GS} =20V; I _D =450A; T _C =25°C
Dynamic characteristics						
Q _G	Total Gate Charge	-	1512	-	nC	V _{DD} =1200V; V _{GS} =-5/+18V; I _D =450A; T _C =25°C
Q _{GD}	Gate-drain Charge	-	450	-		
Source-drain diode						
Q _{RR}	Reverse Recovery Charge	-	8262	-	nC	V _{GS} =-5/+18V; I _F =900A; R _{G(off)} =5Ω; V _R =900V; Load=50uH; T _J =25°C

Absolute Maximum Ratings (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-source Voltage	1700	V
V_{GS}	Gate-source Voltage (dynamic)	-10/+22	V
I_D	Drain Current (continuous)	900	A
I_{DM}	Drain Current (pulsed)	1800	A
T_{op}, T_{stg}	Operating and Storage Temperature Range	-40 to +175	$^{\circ}\text{C}$
T_J	Junction Temperature	175	$^{\circ}\text{C}$
L_{Stray}	Stray Inductance	20	nH
V_{isol}	Isolation Test Voltage (DC; 2mA; t=10s)	4.2	kV
$R_{th Jh}$	Thermal Resistance, Junction-to-Heatsink	0.12	$^{\circ}\text{C/W}$

MOSFET Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)						
BV_{DS}	Drain-source Breakdown Voltage	1700	-	-	V	$V_{GS}=0\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	-	-	450	μA	$V_{DS}=1700\text{V}; V_{GS}=0\text{V}$
I_{GSS}	Gate-body Leakage Current	-	-	4.5	μA	$V_{GS}=-10/20\text{V}; V_{DS}=0\text{V}$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	-	4.0	V	$V_{DS}=V_{GS}; I_D=90\text{mA}$
$R_{DS(on)}$	Static Drain-source on Resistance	-	2.8	3.4	$\text{m}\Omega$	$V_{GS}=20\text{V}; I_D=450\text{A}$
$V_{GS(on)}$	Recommended Turn-on Voltage	-	18	-	V	Static
$V_{GS(off)}$	Recommended Turn-off Voltage	-	-5	-	V	
R_G	Gate Resistance	-	0.4	-	Ω	$V_{AC}=25\text{mV}; f=1\text{MHz}$
Dynamic characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)						
C_{iss}	Input Capacitance	-	58.2	-	nF	$V_{DS}=1200\text{V}; f=100\text{kHz}; V_{AC}=25\text{mV}$
C_{oss}	Output Capacitance	-	1.8	-		
C_{rss}	Reverse Transfer Capacitance	-	144	-	pF	
E_{on}	Turn-on Energy	-	82	-	mJ	$V_{DD}=900\text{V}; V_{GS}=-5/+18\text{V}; I_D=900\text{A}; R_{G(ext)}=5\Omega; \text{Load}=50\mu\text{H}$
E_{off}	Turn-off Energy	-	119	-		
Q_{GS}	Gate-source Charge	-	468	-	nC	$V_{DD}=1200\text{V}; V_{GS}=-5/+18\text{V}; I_D=450\text{A}$
Q_{GD}	Gate-drain Charge	-	450	-		
Q_G	Total Gate Charge	-	1512	-		
$t_{d(on)}$	Turn-on Delay Time	-	143	-	ns	$V_{DD}=900\text{V}; V_{GS}=-5/+18\text{V}; I_D=900\text{A}; R_{G(ext)}=5\Omega; \text{Load}=50\mu\text{H}$
t_r	Rise Time	-	143	-		
$t_{d(off)}$	Turn-off Delay Time	-	520	-		
t_f	Fall Time	-	154	-		

Body Diode Characteristics (at T_J=25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
V _{FSD}	Forward Voltage	-	3.9	6	V	V _{GS} =0V; I _F =450A
I _S	Continuous Diode Forward Current	-	450	-	A	V _{GS} =0V; T _C =25°C
t _{RR}	Reverse Recovery Time	-	110	-	ns	V _{GS} =-5/+18V; I _F =900A; R _{G(off)} =5Ω; V _R =900V; Load=50μH
Q _{RR}	Reverse Recovery Charge	-	8262	-	nC	
I _{RRM}	Peak Reverse Recovery Current	-	328	-	A	

NTC Thermistor Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
R ₂₅	Rated Resistance	-	5.00	-	kΩ	T _{NTC} =25°C
ΔR/R	Deviation of R ₁₀₀	-5	-	5	%	T _{NTC} =100°C; R ₁₀₀ =493.3Ω
B _{25/50}	Beta Value for 25°C to 50°C	-	3375	-	K	R ₂ =R ₂₅ exp [B _{25/50} (1/T ₂ - 1/ (298.15K))]
B _{25/80}	Beta Value for 25°C to 80°C	-	3414	-	K	R ₂ =R ₂₅ exp [B _{25/80} (1/T ₂ - 1/ (298.15K))]
B _{25/100}	Beta Value for 25°C to 100°C	-	3436	-	K	R ₂ =R ₂₅ exp [B _{25/100} (1/T ₂ - 1/ (298.15K))]

Typical Performance

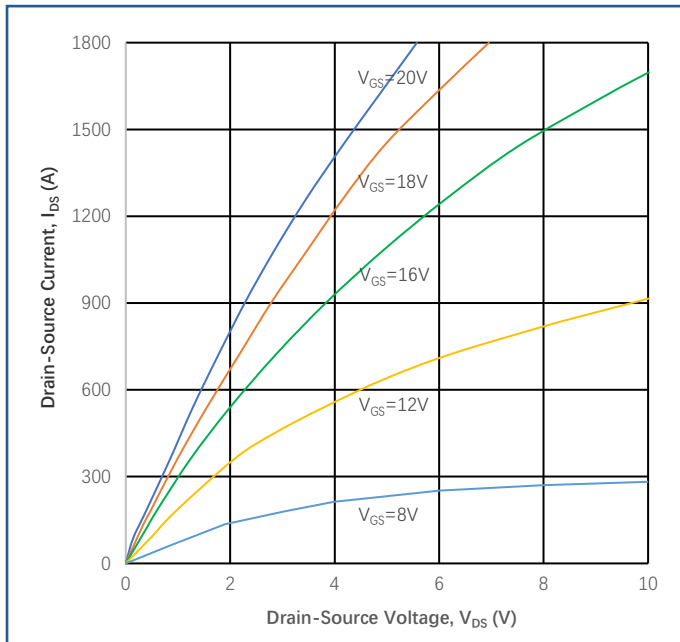


Figure 1
Output Characteristics ($T_J = 25\text{ }^{\circ}\text{C}$)

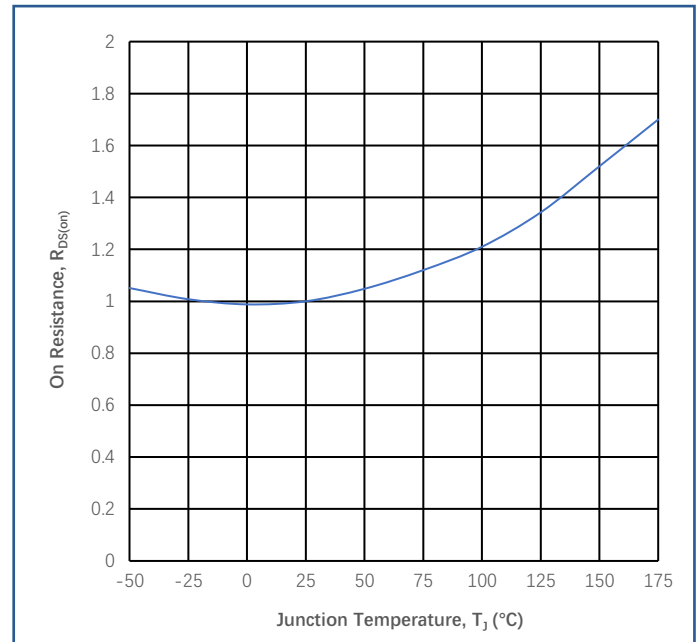


Figure 2
Normalized On-resistance vs. Temperature

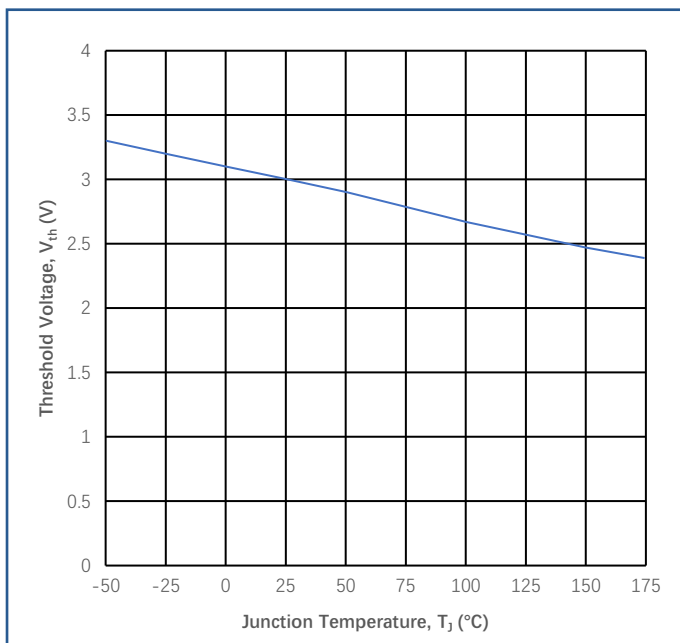


Figure 3
Threshold Voltage vs. Temperature

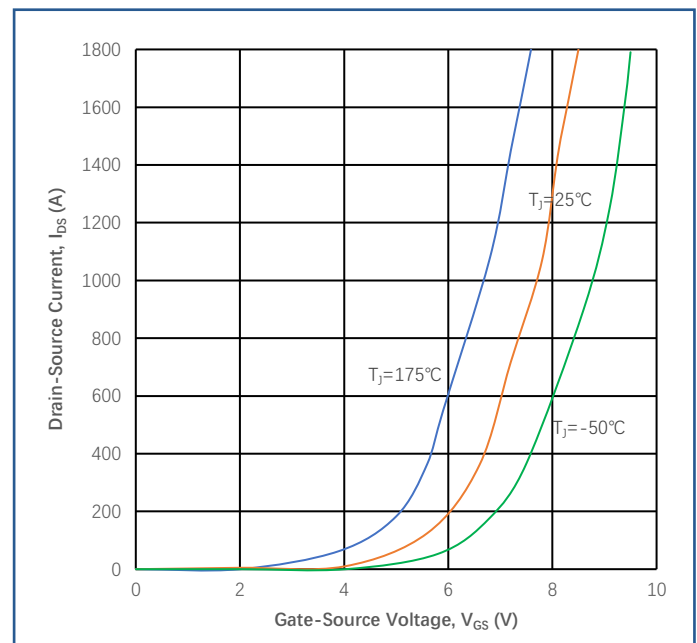


Figure 4
Transfer Characteristic for Various T_J

Typical Performance

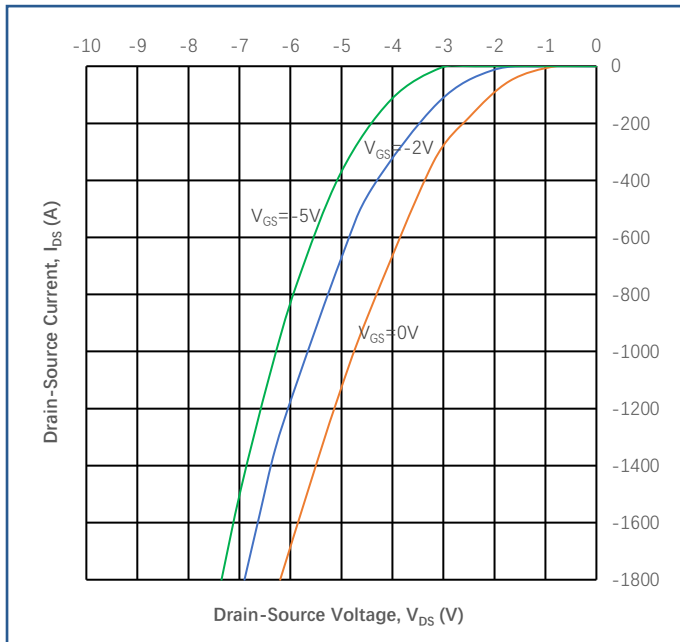


Figure 5
Diode Characteristic at 25 °C

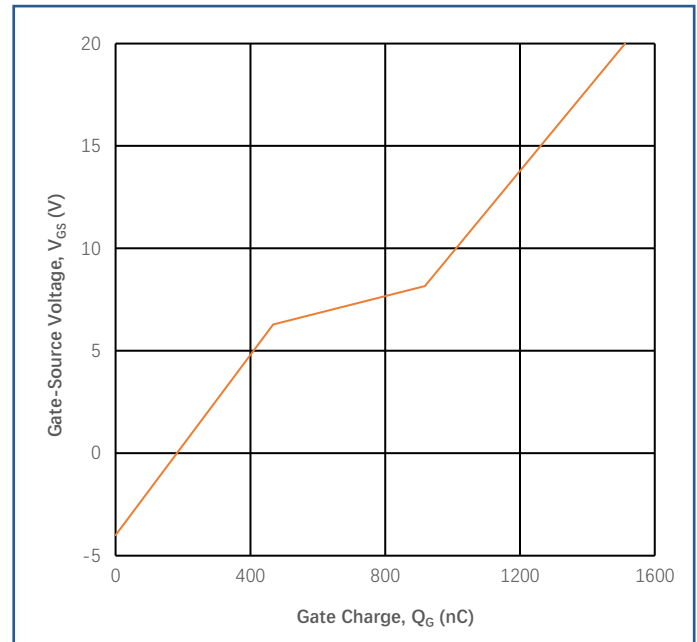


Figure 6
Typical Gate Charge Characteristics

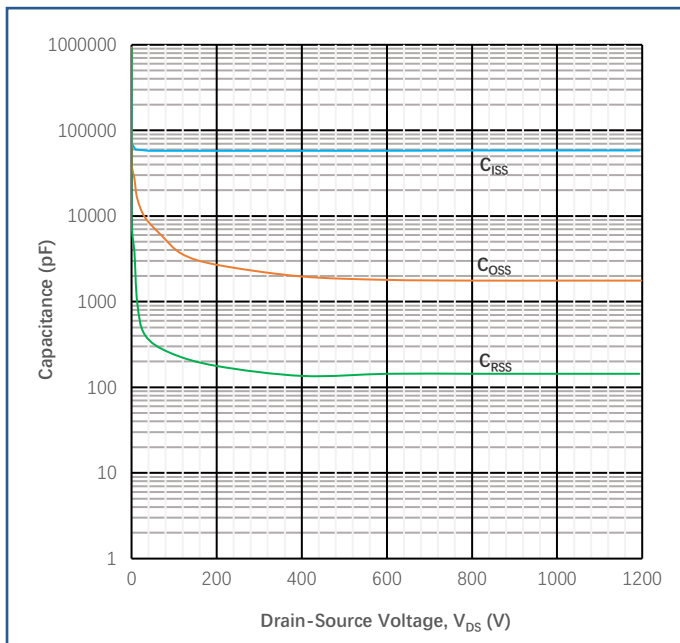


Figure 7
Typical Capacitances vs. Drain-source Voltage

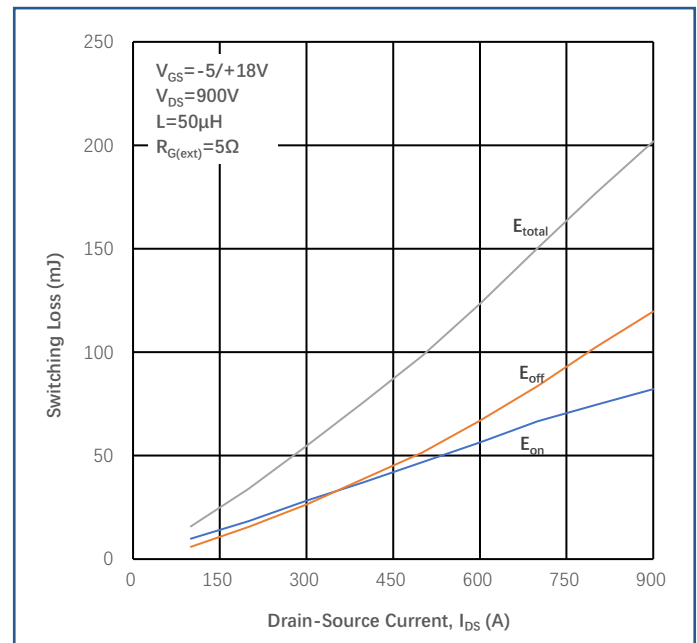


Figure 8
Inductive Switching Energy vs. Drain Current

Typical Performance

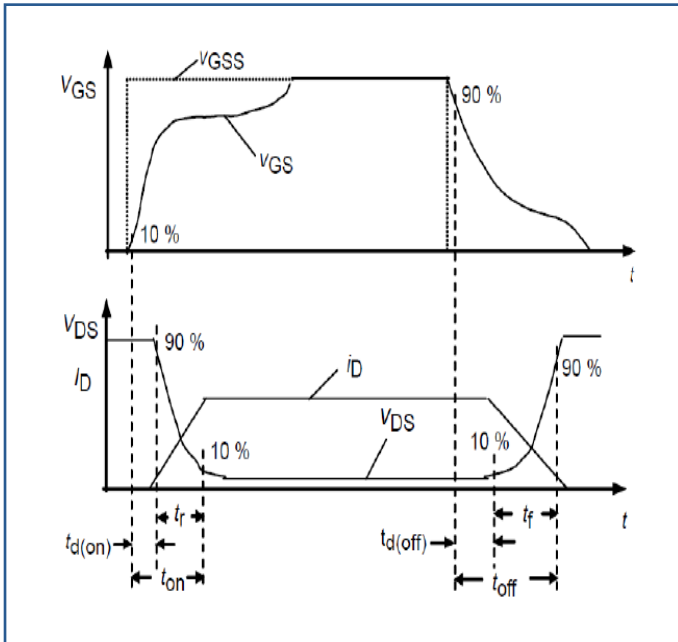


Figure 9

Switching Time Description

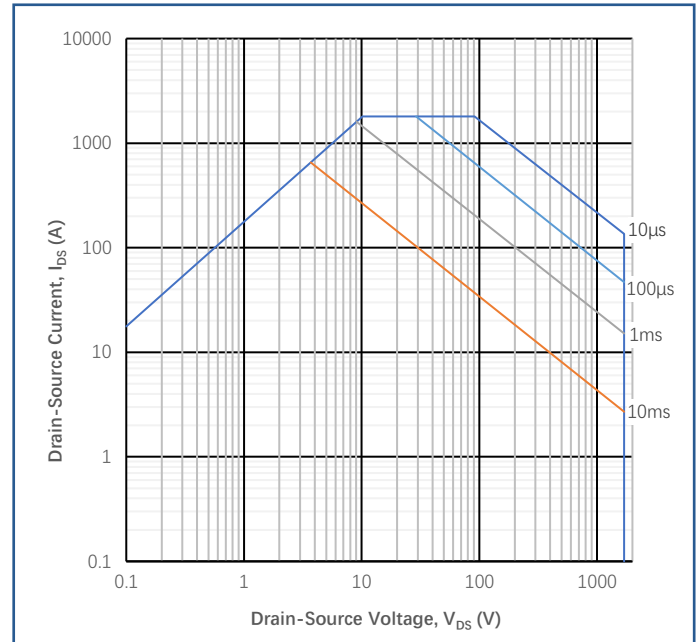
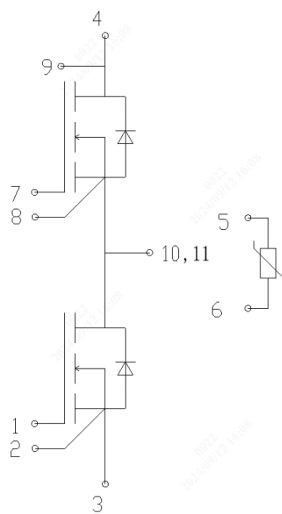


Figure 10

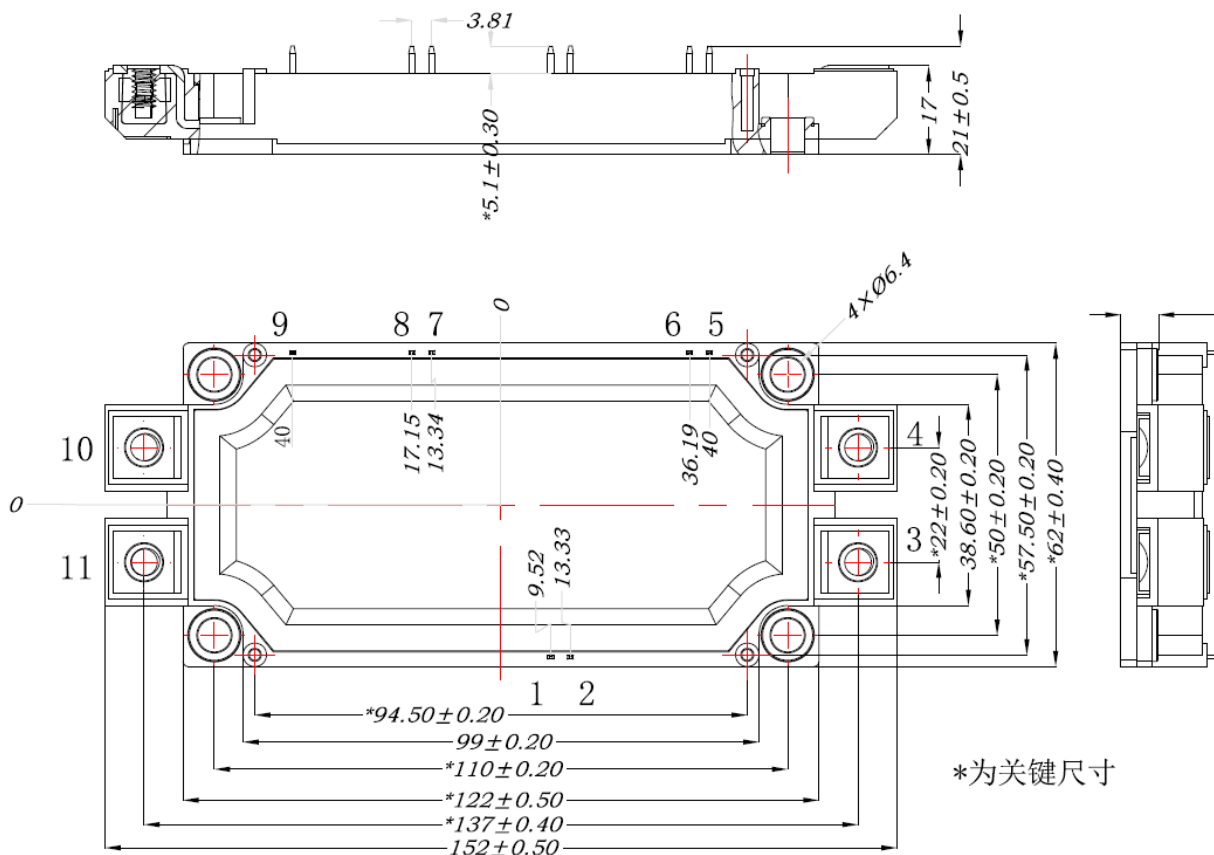
Safe Operating Area

Circuit Diagram Headline



Package Dimensions (mm)

Package Type: MED



未标注线性公差按 GB/1804-2000c 级执行	公差分段	0.5-3	3-6	6-30	30-120	120-400
	c 级	±0.2	±0.3	±0.5	±0.8	±1.2

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